What is claimed is:

1. A focal plane array (FPA) camera comprising:

(I) a voltage source adapted to supply a positive bias voltage and a negative bias voltage, the voltage source comprising:

(IA) a positive terminal; and

(IB) a negative terminal;

(II) a top contact coupled to the positive terminal of the voltage source;

(III) a bottom contact coupled to the negative terminal of the voltage source;

(IV) a substantially-transparent substrate coupled to the bottom contact, the substantially-transparent substrate being adapted to admit light; and

(V) a matrix of detectors, each detector comprising:

(VA) a top surface coupled to the top contact;

(VB) a bottom surface coupled to the substantially-transparent substrate, the bottom surface being substantially parallel to the top surface;

(VC) side surfaces extending from the top surface to the bottom surface, each side surface being substantially non-parallel to an opposing side surface; and

(VD) first-wavelength quantum-well infrared photodetector (QWIP) elements, each first-wavelength QWIP element being adapted to detect energy at a first range of wavelengths when the voltage source supplies the positive bias; and

(VE) second-wavelength QWIP elements, each second-wavelength QWIP element being adapted to detect energy at a second range of wavelengths when the

voltage source supplies the negative bias, the second range of wavelengths being different from the first range of wavelengths.

2. The camera of claim 1:

wherein each first-wavelength QWIP element is a first quantum well adapted to detect energy at a first wavelength;

wherein each second-wavelength QWIP element is a second quantum well adapted to detect energy at a second wavelength; and

wherein the first quantum well and the second quantum well are separated by a blocking barrier.

3. The camera of claim 1:

wherein each first-wavelength QWIP element is a first superlattice of quantum wells; and

wherein each second-wavelength QWIP element is a second superlattice of quantum wells.

4. A multi-wavelength detector system comprising:

(I) a focal plane array (FPA) camera comprising:

(IA) a voltage source adapted to supply a first bias voltage, the voltage source further being adapted to supply a second bias voltage;

(IB) first-wavelength detectors coupled to the voltage source, the first-wavelength detectors having non-parallel sides, the first-wavelength detectors being adapted to detect energy at a first range of wavelengths when the voltage source supplies the first bias voltage, the first-wavelength detectors further being adapted to generate photocurrents proportional to the detected energy at the first range of wavelengths; and

(IC) second-wavelength detectors being coupled to the voltage source, the second-wavelength detectors having non-parallel sides, the second-wavelength detectors being adapted to detect a second range of wavelengths when the voltage source supplies the second bias voltage, the second-wavelength detectors further being adapted to generate photocurrents proportional to the detected energy at the second range of wavelengths; and

(II) a processor coupled to the FPA camera, the processor being configured to generate a first-wavelength two-dimensional image, the first-wavelength two-dimensional image being generated from the photocurrents proportional to the detected energy at the first range of wavelengths, the processor further being configured to generate a second-wavelength two-dimensional image, the second-wavelength two-dimensional image being generated from the photocurrents proportional to the detected energy at the second range of wavelengths.

5. The system of claim 4, further comprising:

a display adapted to display the first-wavelength two-dimensional image, the display further being adapted to display the second-wavelength two-dimensional image.

6. The system of claim 5, wherein the display is further adapted to substantially concurrently display the first-wavelength two-dimensional image and the second-wavelength two-dimensional image.

7. A detector comprising:

a first contact;

a second contact;

a substantially-transparent substrate coupled to the second contact, the substantially-transparent substrate being configured to admit light;

a voltage source electrically coupled to the first contact and the second contact, the voltage source being adapted to supply a first bias voltage between the first contact and the second contact, the voltage source further being adapted to supply a second bias voltage between the first contact and the second contact;

a top coupled to the first contact;

a bottom coupled to the substantially-transparent substrate, the bottom adapted to receive the light admitted through the substantially-transparent substrate;

sides extending from the top to the bottom, each side being substantially non-perpendicular to the bottom, each side being adapted to redirect the admitted light;

a first-wavelength quantum-well infrared photodetector (QWIP) element adapted to detect energy proportional to a first range of wavelengths when the voltage source supplies the first bias voltage; and

a second-wavelength QWIP element adapted to detect energy proportional to a second range of wavelengths when the voltage source supplies the second bias voltage.

8. The detector of claim 7:

wherein the first contact is a metal contact; and

wherein the second contact is a metal contact.

9. The detector of claim 7, wherein each side is substantially non-parallel to an opposing side.

10. The detector of claim 7:

wherein each first-wavelength QWIP element is a first quantum well adapted to detect energy at a first wavelength;

wherein each second-wavelength QWIP element is a second quantum well adapted to detect energy at a second wavelength; and

wherein the first quantum well and the second quantum well are separated by a blocking barrier.

11. The detector of claim 7:

wherein each first-wavelength QWIP element is a first superlattice of quantum wells, the first superlattice of quantum wells being adapted to detect energy at a first range of wavelengths; and

wherein each second-wavelength QWIP element is a second superlattice of quantum wells, the second superlattice of quantum wells being adapted to detect energy at a second range of wavelengths.

12. A voltage-tunable multi-color infrared (IR) detector element comprising:

a substantially-planar surface adapted to admit light; and

means for redirecting the admitted light.

13. A voltage-tunable multi-color infrared (IR) detector element comprising:

a substantially-planar surface adapted to admit light; and

sides extending from the substantially-planar surface, each side being substantially non-perpendicular to the substantially-planar surface, each side being adapted to redirect the light admitted through the substantially-planar surface.

14. The detector element of claim 13, wherein each side is substantially non-parallel to an opposing side.

15. The detector element of claim 13, wherein each voltage-tunable multi-color IR detector comprises:

a first superlattice of quantum wells, the first superlattice being adapted to detect energy at a first range of wavelengths; and

a second superlattice of quantum wells, the second superlattice being adapted to detect energy at a second range of wavelengths.

16. The detector element of claim 13, wherein each voltage-tunable multi-color IR detector comprises:

a first quantum well adapted to detect energy at a first wavelength; and

a second quantum well adapted to detect energy at a second wavelength.

17. A light-detection method comprising the steps of:

receiving incident radiation;

reflecting the incident radiation at an angled surface; and

directing the reflected radiation through a voltage-tunable multi-color infrared (IR) detector element.

18. The method of claim 17, further comprising the step of:

supplying a first bias voltage to the voltage-tunable multi-color IR detector element to detect energy at a first range of wavelengths.

19. The method of claim 18, further comprising the step of:

generating a first-wavelength image, the first-wavelength image being generated from the detected energy at the first range of wavelengths.

20. The method of claim 18, further comprising the step of:

supplying a second bias voltage to the voltage-tunable multi-color IR detector element to detect energy at a second range of wavelengths.

21. The method of claim 20, further comprising the step of:

generating a first-wavelength image, the first-wavelength image being generated from the detected energy at the first range of wavelengths; and

generating a second-wavelength image, the second-wavelength image being generated from the detected energy at the second range of wavelengths.